UPG60N60E

**Preliminary** 

Insulated Gate Bipolar Transistor

# 600V, SMPS N-CHANNEL IGBT

#### **■ DESCRIPTION**

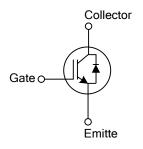
The UTC **UPG60N60E** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

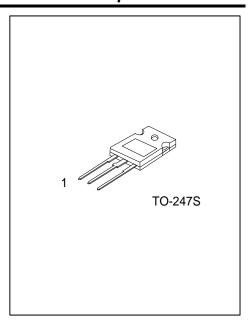
The UTC **UPG60N60E** is suitable for high voltage switching, high frequency switch mode power supplies.

## **■ FEATURES**

- \*  $V_{CE(SAT)} \le 2.5 V @ I_C=60A, V_{GE}=15 V$
- \* High switching speed
- \* High input impedance
- \* Low conduction loss

## ■ SYMBOL





# ORDERING INFORMATION

Ordering Number		Daakassa	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UPG60N60EL-T47S-T	UPG60N60EG-T47S-T	TO-247S	G	С	Е	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter

UPG60N60EG-T47S-T (1)Packing Type (1) T: Tube (2)Package Type (2) T47S: TO-247S (3)Green Package (3) G: Halogen Free and Lead Free, L: Lead Free

# **■ MARKING**



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# ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	600	V
Gate to Emitter Voltage Continuous		$V_{GES}$	±20	V
Cantinuous Callacter Current	T <sub>C</sub> =25°C		120	Α
Continuous Collector Current	T <sub>C</sub> =100°C	I <sub>C</sub>	60	Α
Collector Current Pulsed (Note 2)		I <sub>CM</sub>	200	Α
0 11 5 10 1	T <sub>C</sub> =25°C		60	Α
Continuous Forward Current	T <sub>C</sub> =100°C	l <sub>F</sub>	30	Α
Forward Current Pulsed		I <sub>FM</sub>	136	Α
Peak Diode Recovery dv/dt (Note 3)		dv/dt	7.1	V/ns
Power Dissipation		$P_{D}$	270	W
Junction Temperature		$T_J$	-55 ~ <b>+</b> 150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
  - 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
  - 3.  $I_F \le 30A$ , di/dt  $\le 200A/\mu s$ ,  $V_{CC} \le BV_{CES}$ , Starting  $T_J = 25$ °C

## THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	$\theta_{JC}$	0.46	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	I <sub>C</sub> =250μA, V <sub>GE</sub> =0V		600			V
Collector-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> =600V, V <sub>GE</sub> =0V				10	μΑ
Gate to Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±400	nA
ON CHARACTERISTICS							
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =60A, V <sub>GE</sub> =15V	T <sub>J</sub> =25°C		2.0	2.5	V
			T <sub>J</sub> =150°C		2.3		V
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>		4.0		6.5	V
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>IES</sub>				1905		pF
Output Capacitance	C <sub>OES</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz			206		pF
Reverse Transfer Capacitance	C <sub>RES</sub>	7			36		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge	$Q_{G}$	I <sub>C</sub> =60A, V <sub>CE</sub> =100V, V <sub>GE</sub> =10V			64		nC
Gate-Emitter Charge	$Q_{GE}$				12.7		nC
Gate-Collector Charge	$Q_{GC}$				30		nC
Current Turn-On Delay Time	t <sub>D(ON)</sub>				73		ns
Current Rise Time	t <sub>R</sub>	$I_{C}$ =60A, $V_{CE}$ =50V, $V_{GE}$ =15V, $I_{C}$ =10 $I_{C}$			86		ns
Current Turn-Off Delay Time	t <sub>D(OFF)</sub>				137		ns
Current Fall Time	t <sub>F</sub>	3			244		ns
DRAIN-SOURCE DIODE CHARACTER	ISTICS		A 112	2			
Forward Voltage Drop	$V_{FM}$	I <sub>F</sub> =12A				2.8	V
Reverse Recovery Time	trr	1 404 41/45 4004/40	14 20014		95		ns
Reverse Recovery Charge	$Q_{rr}$	I <sub>F</sub> =12A, dI/dt=100A/µS, V <sub>CC</sub> =400V			257		nC
Note: Pulse Test: Pulse width ≤ 50 µs.	-4	THE FIVING					
		F=12A, d  /d=100A/µ\$,					
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## **■ TEST CIRCUIT AND WAVEFORMS**

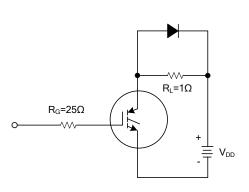


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

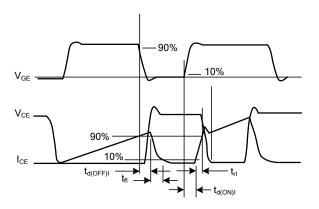


Fig 2. SWITCHING TEST WAVEFORMS

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